

**BCW67 SERIES  
BCW68 SERIES**

**SURFACE MOUNT  
PNP SILICON TRANSISTOR**



**MAXIMUM RATINGS (T<sub>A</sub>=25°C)**

	<b>SYMBOL</b>	<b>BCW67</b>	<b>BCW68</b>	<b>UNITS</b>
Collector-Base Voltage	V <sub>CBO</sub>	45	60	V
Collector-Emitter Voltage	V <sub>CEO</sub>	32	45	V
Emitter-Base Voltage	V <sub>EBO</sub>		5.0	V
Collector Current	I <sub>C</sub>		800	mA
Peak Collector Current	I <sub>CM</sub>		1.0	A
Base Current	I <sub>B</sub>		100	mA
Peak Base Current	I <sub>BM</sub>		200	mA
Power Dissipation	P <sub>D</sub>		350	mW
Operating and Storage				
Junction Temperature	T <sub>J</sub> , T <sub>stg</sub>		-65 to +150	°C
Thermal Resistance	θ <sub>JA</sub>		357	°C/W

**ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C unless otherwise noted)**

<b>SYMBOL</b>	<b>TEST CONDITIONS</b>	<b>MIN</b>	<b>TYP</b>	<b>MAX</b>	<b>UNITS</b>
I <sub>CBO</sub>	V <sub>CB</sub> =Rated V <sub>CEO</sub>			20	nA
I <sub>CBO</sub>	V <sub>CB</sub> = Rated V <sub>CEO</sub> , T <sub>A</sub> =150°C			20	μA
I <sub>EBO</sub>	V <sub>EB</sub> =4.0V			20	nA
BV <sub>CBO</sub>	I <sub>C</sub> =10μA (BCW67)	45			V
BV <sub>CBO</sub>	I <sub>C</sub> =10μA (BCW68)	60			V
BV <sub>CEO</sub>	I <sub>C</sub> =10mA (BCW67)	32			V
BV <sub>CEO</sub>	I <sub>C</sub> =10mA (BCW68)	45			V
BV <sub>EBO</sub>	I <sub>E</sub> =10μA	5.0			V
V <sub>CE(SAT)</sub>	I <sub>C</sub> =100mA, I <sub>B</sub> =10mA			0.3	V
V <sub>CE(SAT)</sub>	I <sub>C</sub> =500mA, I <sub>B</sub> =50mA			0.7	V
V <sub>BE(SAT)</sub>	I <sub>C</sub> =100mA, I <sub>B</sub> =10mA			1.25	V
V <sub>BE(SAT)</sub>	I <sub>C</sub> =500mA, I <sub>B</sub> =50mA			2.0	V
f <sub>T</sub>	V <sub>CE</sub> =5.0V, I <sub>C</sub> =50mA, f=20MHz		200		MHz
C <sub>c</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1.0MHz		6.0		pF
C <sub>e</sub>	V <sub>EB</sub> =0.5V, I <sub>C</sub> =0, f=1.0MHz		60		pF

	<b>BCW67A</b>		<b>BCW67B</b>		<b>BCW67C</b>	
	<b>BCW68F</b>		<b>BCW68G</b>		<b>BCW68H</b>	
	<b>MIN</b>	<b>MAX</b>	<b>MIN</b>	<b>MAX</b>	<b>MIN</b>	<b>MAX</b>
h <sub>FE</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =100μA	35		50		80
h <sub>FE</sub>	V <sub>CE</sub> =1.0V, I <sub>C</sub> =10mA	75		120		180
h <sub>FE</sub>	V <sub>CE</sub> =1.0V, I <sub>C</sub> =100mA	100	250	160	400	250
h <sub>FE</sub>	V <sub>CE</sub> =2.0V, I <sub>C</sub> =500mA	35		60		100

R1 (20-February 2003)

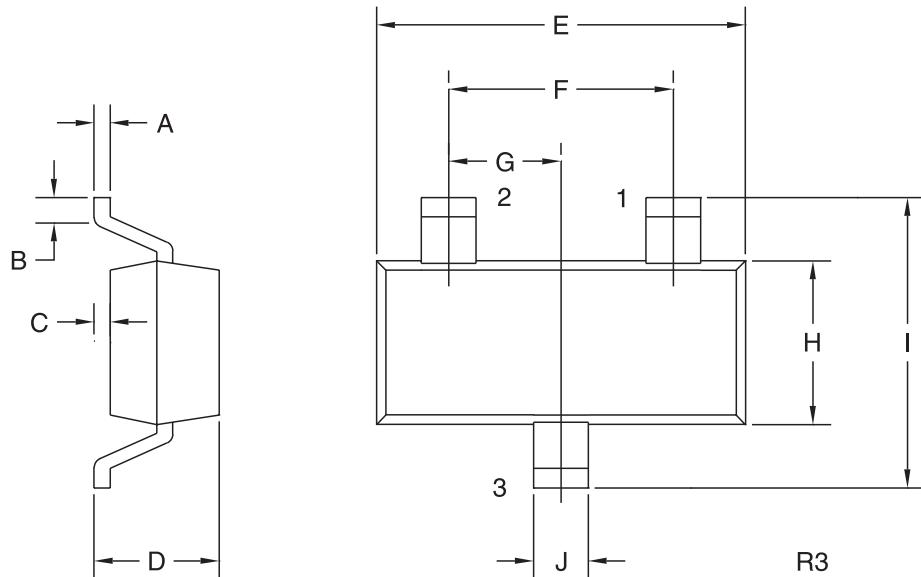
**Central**<sup>TM</sup>  
**Semiconductor Corp.**

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR BCW67 and BCW68 Series types are PNP Silicon Transistors manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for general purpose switching and amplifier applications.

**MARKING CODE: PLEASE SEE MARKING CODE TABLE ON FOLLOWING PAGE**

SOT-23 CASE - MECHANICAL OUTLINE



**LEAD CODE:**

- 1) BASE
- 2) Emitter
- 3) Collector

DEVICE	MARKING CODE
BCW67A	DA
BCW67B	DB
BCW67C	DC
BCW68F	DF
BCW68G	DG
BCW68H	DH

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075	-	1.90	-
G	0.037	-	0.95	-
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)